

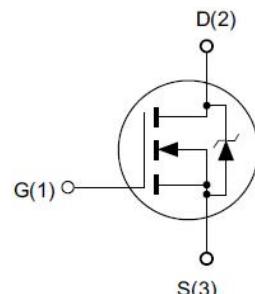


MPP10N65

N-Channel Power MOSFET

Features

- ◆ 650V, 10A, $R_{DS(ON)}$ (Typ.) = 0.80Ω@VGS = 10V.
- ◆ Low Crss
- ◆ Fast Switching
- ◆ 100% Avalanche Tested



Application

- ◆ Adapter
- ◆ LCD/PDP Adapter
- ◆ E-Bike Charger

Absolute Maximum Ratings $T_c = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Limit	Unit
		PTO-252	
V_{DS}	Drain-Source Voltage ^a	650	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-Continuous, $T_c = 25^\circ C$	10	A
	Drain Current-Continuous, $T_c = 100^\circ C$	5.5	A
I_{DM}	Drain Current-Pulsed ^b	40	A
P_D	Maximum Power Dissipation @ $T_j = 25^\circ C$	100	W
E_{AS}	Single Pulsed Avalanche Energy ^d	405	mJ
T_j, T_{STG}	Operating and Store Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-Case Max.	1.25	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient Max.	62.5	°C/W

Electrical Characteristics $T_j = 25^\circ C$ unless otherwise noted

Off Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	650	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 650V, V_{GS} = 0V$	-	-	1	μA
I_{GSS}	Forward Gate Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 30V$	-	-	± 100	nA



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■ On Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	2	-	4	V
$R_{DS(on)}$	Static Drain-Source On-Resistance ^c	$V_{GS} = 10V$, $I_D = 5A$	-	0.80	1.00	Ω

■ Dynamic Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
C_{iss}	Input Capacitance	$V_{DS} = 25V$, $V_{GS} = 0V$, $f = 1.0MHz$	-	1595	-	pF
C_{oss}	Output Capacitance		-	134	-	pF
C_{rss}	Reverse Transfer Capacitance		-	6.6	-	pF

■ On Characteristics

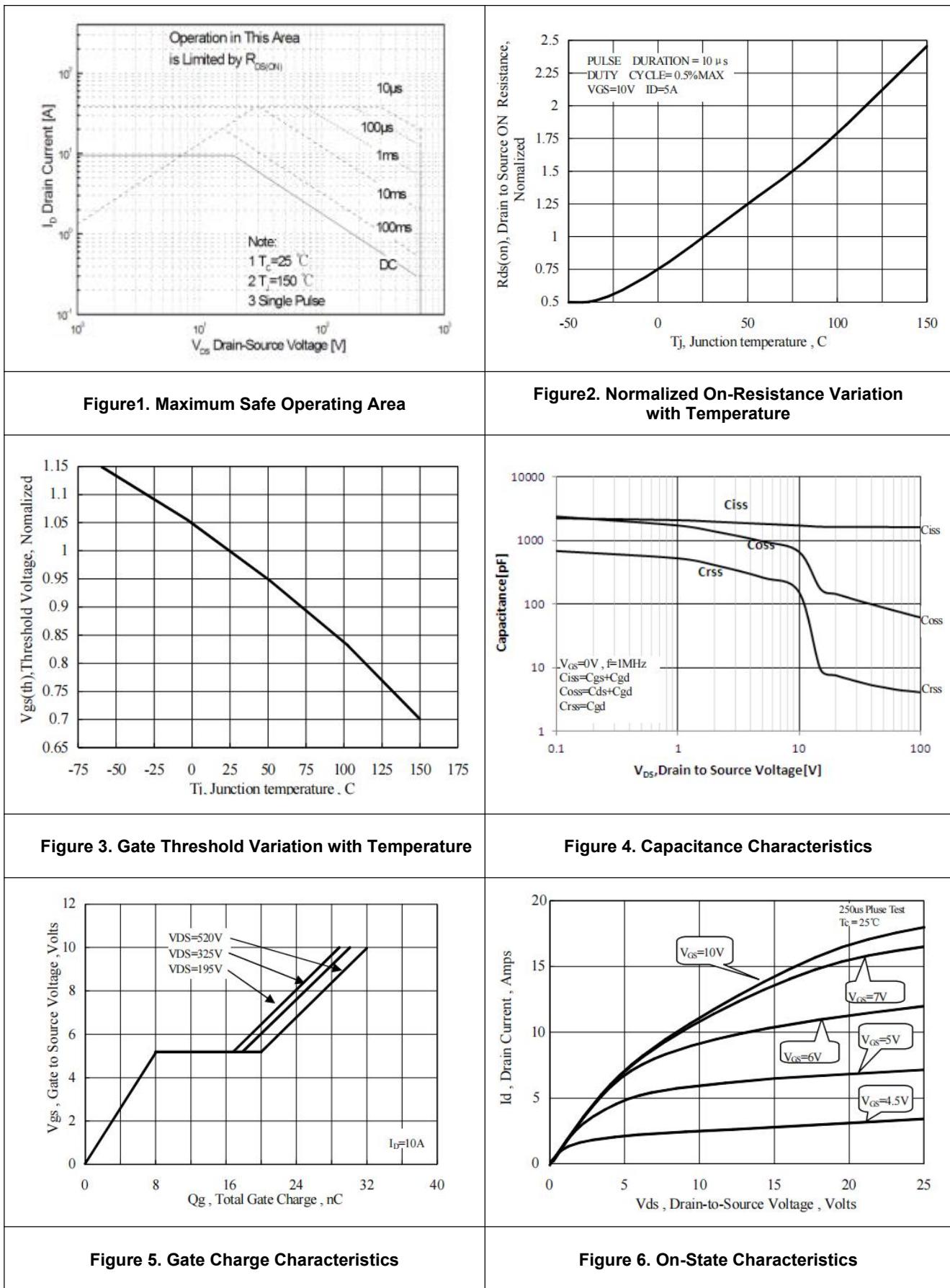
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 325V$, $I_D = 10A$, $R_G = 25\Omega$, $V_{GS} = 10V$	-	25	-	ns
t_r	Turn-On Rise Time		-	21	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	50	-	ns
t_f	Turn-Off Fall Time		-	23	-	ns
Q_g	Total Gate Charge	$V_{DS} = 325V$, $I_D = 10A$, $V_{GS} = 10V$	-	31.9	-	nC
Q_{gs}	Gate-Source Charge		-	8.1	-	nC
Q_{gd}	Gate-Drain Charge		-	11.9	-	nC

■ Drain-Source Diode Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
I_s	Drain-Source Diode Forward Continuous Current	$V_{GS} = 0V$	-	-	10	A
I_{SM}	Maximum Pulsed Current	$V_{GS} = 0V$	-	-	40	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0V$, $I_s = 10A$	-		1.4	V
T_{rr}	Body Diode Reverse Recovery Time	$di/dt = 100A/\mu s$ $I_s = 10A$, $V_{GS} = 0V$	-	498	-	ns
Q_{rr}	Reverse Recovery Charge		-	3039	-	nC

Notes:

- a. $T_J = +25^\circ C$ to $+150^\circ C$
- b. Repetitive rating; pulse width limited by maximum junction temperature.
- c. Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$
- d. $L = 10mH$, $V_{DD} = 50V$, $I_{as} = 9A$, $R_G = 25\Omega$ Starting $T_J = 25^\circ C$



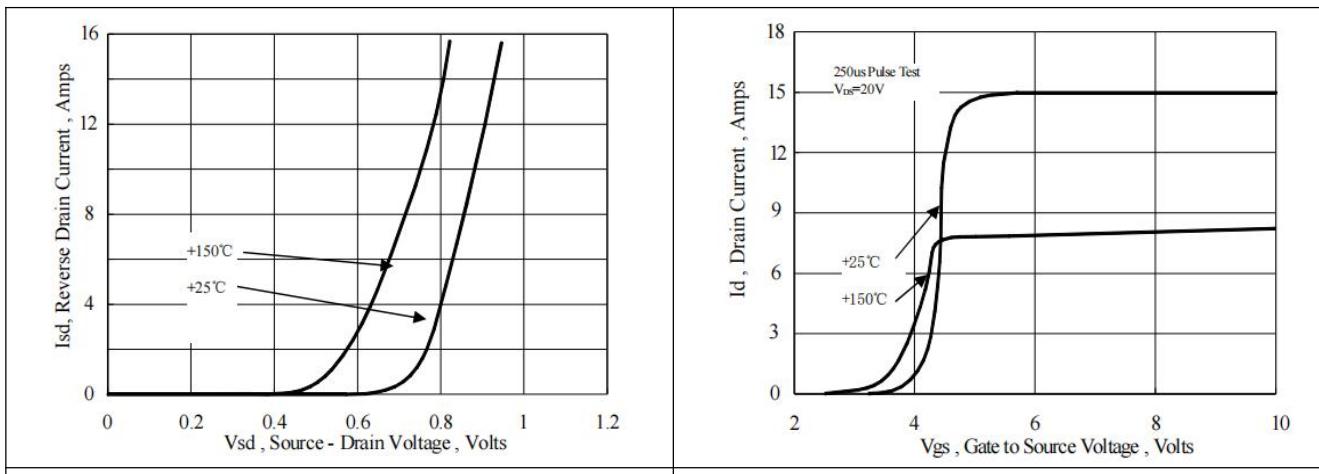


Figure 7. Body Diode Forward Voltage Variation with Source Current

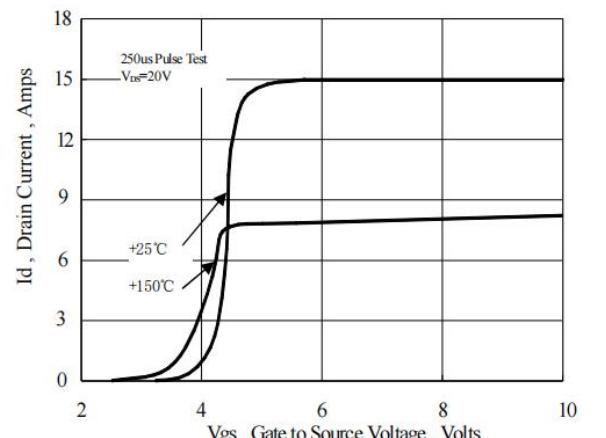


Figure 8. Transfer Characteristics Variation with Source Current

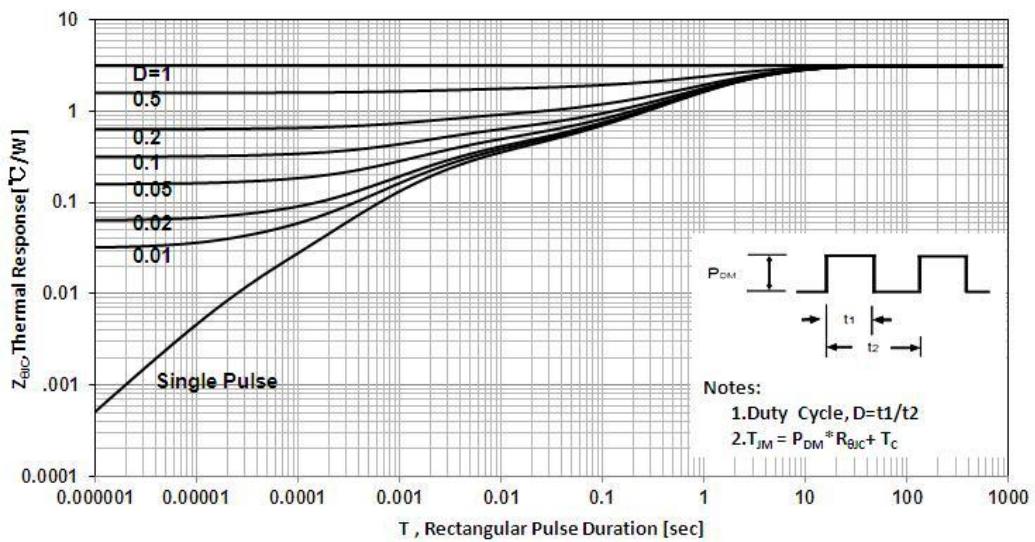
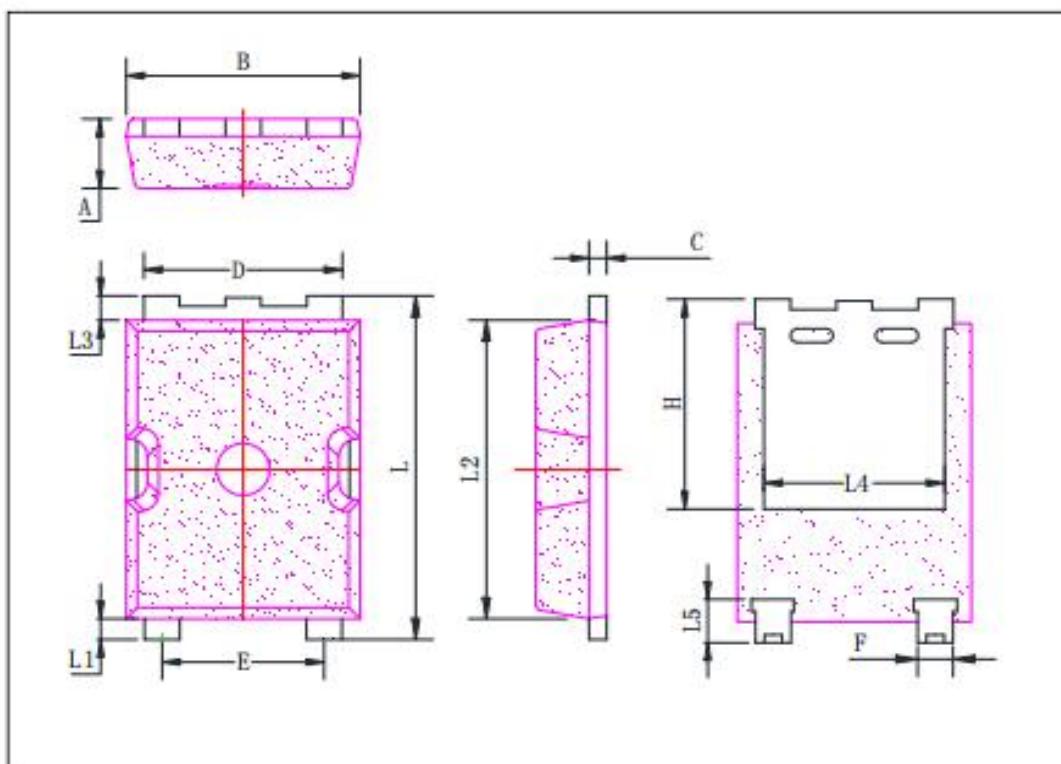


Figure 9. Maximum Effective Thermal Impedance , Junction to Case

■ Package Information



Symbol	Min	Typ	Max
A	1.90	2.00	2.10
B	6.50	6.60	6.70
C	0.45	0.50	0.60
D	5.50	5.60	5.70
E	4.50	4.60	4.70
F	0.90	1.00	1.05
H	5.90	6.05	6.20
L	9.80	9.90	10.0
L1	0.50	0.60	0.70
L2	8.50	8.60	8.70
L3	0.60	0.70	0.80
L4	4.65	4.80	4.90
L5	1.10	1.25	1.40